

# Rr Lapierre

## List of Publications by Year in descending order

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10  
papers

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1040056  
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docs citations

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times ranked

476  
citing authors

#	ARTICLE	IF	CITATIONS
1	Control of GaP nanowire morphology by group V flux in gas source molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2017, 462, 29-34.	1.5	17
2	Facilitating growth of InAs-InP core-shell nanowires through the introduction of Al. <i>Journal of Crystal Growth</i> , 2012, 345, 11-15.	1.5	14
3	Impedance spectroscopy characterization of GaAs nanowire bundles grown by metal-catalyzed molecular beam epitaxy. <i>Journal of Alloys and Compounds</i> , 2010, 495, 443-445.	5.5	2
4	Au-assisted growth of GaAs nanowires by gas source molecular beam epitaxy: Tapering, sidewall faceting and crystal structure. <i>Journal of Crystal Growth</i> , 2008, 310, 356-363.	1.5	80
5	Growth mechanisms of GaAs nanowires by gas source molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2006, 286, 394-399.	1.5	111
6	The formation of supported monodisperse Au nanoparticles by UV/ozone oxidation process. <i>Applied Surface Science</i> , 2006, 253, 2348-2354.	6.1	28
7	Layer-by-layer and step-flow growth mechanisms in GaAsP/GaP nanowire heterostructures. <i>Journal of Materials Research</i> , 2006, 21, 2801-2809.	2.6	47
8	Growth mechanisms of III-V compounds by atomic hydrogen-assisted epitaxy. <i>Journal of Crystal Growth</i> , 1998, 191, 319-331.	1.5	11
9	Lateral composition modulation in InGaAsP strained layers and quantum wells grown on (100) InP by gas source molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 1996, 158, 6-14.	1.5	45
10	Spinodal-like decomposition of grown by gas source molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 1995, 155, 1-15.	1.5	67